

Fast switching diode

Features:

- 1700V technology, Emitter Controlled Diode 3th generation, 200 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient
- Qualified according to JEDEC for target applications

Recommended for:

power modules



Applications:

resonant applications, drives

Chip Type	V _R	<i>I</i> _{Fn} ¹⁾	Die Size	Package
SIDC130D170H	1700V	235A	16.3 x 8 mm ²	sawn on foil

¹⁾ nominal forward current at Tc = 100°C, not subject to production test - verified by design/characterisation

Mechanical Parameters

Die size		16.3 x 8		
Area total		130.4		
Anode pad size		14.28 x 5.98		
Thickness		200	μm	
Wafer size		150	mm	
Max. possible chips pe	er wafer	100		
Passivation frontside		Photoimide		
Pad metal		3200 nm AlSiCu		
Backside metal		Ni Ag –system		
Die bond		Electrically conductive epoxy glue and soft solder		
Wire bond		Al, ≤500μm		
Reject ink dot size		Ø 0.65mm; max 1.2mm		
Storage environment	for original and sealed MBB bags	Ambient atmosphere air, Temperature 17°C – 2 < 6 month		
	for open MBB bags	Acc. to IEC62258-3: Atmosphere >99% Nitrogen or inert gas, Humidity <25%RH, Temperature 17°C – 25°C, < 6 month		



Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	<i>T</i> _{vj} = 25 °C	1700	V
Continuous forward current	I _F	<i>T</i> _{vj} < 150°C	1)	_
Maximum repetitive forward current ²)	I _{FRM}	<i>T</i> _{vj} < 150°C	470	A
Junction temperature range	$T_{\rm vj}$		-40+175	00
Operating junction temperature	$T_{\rm vj}$		-40+150	°C

¹⁾ depending on thermal properties of assembly

Static Characteristics (tested on wafer), $T_{vj} = 25$ °C

Doromotor	Symbol	Conditions	Value			Unit
Parameter			min.	typ.	max.	Onic
Reverse leakage current	I_{R}	V _R =1700V			11	μA
Cathode-Anode breakdown Voltage	V_{BR}	$I_{R}=0.25$ m A	1700			V
Forward voltage drop	V_{F}	I _F =70.5A	1.15	1.35	1.55	V

Electrical Characteristics (not subject to production test - verified by design/characterization)

Parameter		Symbol Conditions	Conditions	Value			Unit
			Conditions	min.	typ.	max.	Offic
Forward voltage	$T_{\rm vj} = 25^{\circ}{\rm C}$	V	1 225A		1.75	2.45	\/
drop	T _{vj} = 150°C	V _F	/ _F =235A		1.8		\ \ \

Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

This chip data sheet refers to the device data sheet	FF1400R17IP4	Rev. 2.2
--	--------------	----------

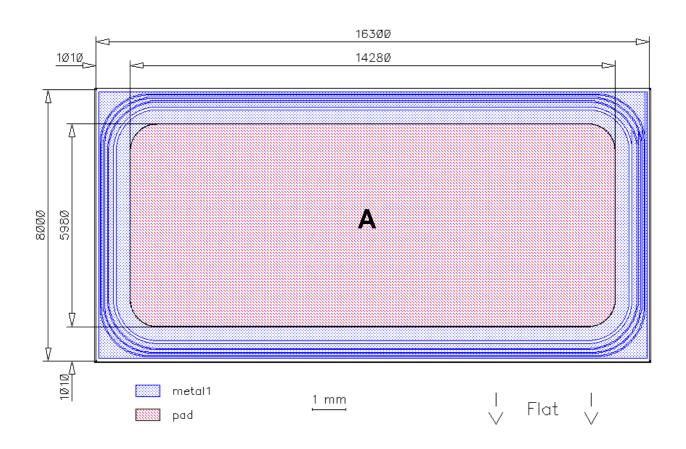
Edited by INFINEON Technologies, IFAG IMM PSD D, L4504A, Edition 1.1, 15.05.2013

²⁾ not subject to production test - verified by design/characterisation



Chip Drawing

Die-Size 16300 um x 8000 um



A: Anode pad



Description
AQL 0,65 for visual inspection according to failure catalogue
Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date

Published by Infineon Technologies AG 81726 Munich, Germany © 2013 Infineon Technologies AG All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Edited by INFINEON Technologies, IFAG IMM PSD D, L4504A, Edition 1.1, 15.05.2013

单击下面可查看定价,库存,交付和生命周期等信息

>>Infineon Technologies(英飞凌)